

NEC

T-41-01

OPTOELECTRONIC DEVICES

Light Emitting Diodes (cont.)

Remote Control

Part Number	Material	Features	Absolute Maximum Ratings (T _a = 25°C)			Typical Characteristics (T _a = 25°C)			
			P _d (mW)	I _F (mA)	T _{stg} (°C)	V _F TYP. (V) (I _F =30 mA)	I _R TYP. (μA) (V _R =3 V)	λ _p TYP. (nm) (I _F =30 mA)	P _o TYP. (mW) (I _F =30 mA)
SE301A	GaAs	High output High reliability	150	100	-65 to +125	1.2 (I _F =50 mA)	0.01	940 (I _F =50 mA)	8 (I _F =50 mA)
SE302A	GaAs	Mini size	75	50	-30 to +80	1.2	0.01	940	1.5
SE303A-C	GaAs	High output Wide radiation angle	150	100	-40 to +100	1.25 (I _F =50 mA)	0.01 (V _R =5 V)	940 (I _F =50 mA)	8 (I _F =50 mA)
SE304	GaAs	Lateral direction output	100	50	-40 to +100	1.2	0.01	940	1.5
SE306	GaAs	Lateral direction output with a lens	100	50	-40 to +100	1.1 (I _F =10 mA)	0.01	940 (I _F =10 mA)	0.5 mW/sr (I _F =10 mA)
SE307-C	GaAs	ULTRA High output Narrow radiation angle	150	100	-40 to +100	1.25 (I _F =50 mA)	0.01 (V _R =5 V)	940 (I _F =50 mA)	30 mW/sr (I _F =50 mA)
SE308	GaAs	Small package Lateral direction output	100	50	-40 to +100	1.14 (I _F =20 mA)	0.01	940 (I _F =20 mA)	0.85 mW/sr (I _F =20 mA)
SE310	GaAs	High output Small package	150	60	-40 to +100	1.25 (I _F =50 mA)	0.01 (V _R =5 V)	940 (I _F =50 mA)	11 mW/sr (I _F =50 mA)
SE313	GaAs	ULTRA High output Middle radiation angle	150	100	-40 to +100	1.25 (I _F =50 mA)	0.01 (V _R =5 V)	940 (I _F =50 mA)	25 mW/sr (I _F =50 mA)
SE1003-C	GaAlAs on GaAs	ULTRA High output Wide radiation angle	150	100	-40 to +100	1.27 (I _F =50 mA)	0.01 (V _R =5 V)	950 (I _F =50 mA)	20 mW/sr (I _F =50 mA)

Avalanche Photo Diodes

Part Number	Absolute Maximum Ratings (T _a = 25°C)			Detecting Area Size (μ m) Typ.	Typical Characteristics (T _a = 25°C)								Remarks	Package Style
	I _F (mA)	I _R (mA)	T _{stg} (°C)		V _{(BR)R} (V) Typ.	I _D (nA)		M Typ.	η (%)		t _r , t _f (ns) Typ.			
						V _R (V)	Max.		λ (nm)	Typ.				
NDL1102	100	—	-65 to +150	ϕ 240	120	V _{(BR)R} -1.0	1.0**	150	630 850	65 65	0.5 10		TO-18 Can	
NDL1202	100	—	-65 to +150	ϕ 240	200	V _{(BR)R} -2.0	1.0**	150	850	70	1.0**		TO-18 Can	
NDL5100	50	0.5	-55 to +125	ϕ 100	29	V _{(BR)R} ×0.9	200	40	1300	75	0.5		TO-18 Can	
NDL5100C	50	0.5	-55 to +125	ϕ 100	29	V _{(BR)R} ×0.9	200	40	1300	75	0.5	Chip on carrier	Surface mount	
NDL5100P	50	0.5	-40 to +70	ϕ 100	29	V _{(BR)R} ×0.9	200	40	1300	75	0.5	With GI-50/125	Pigtail	
NDL5102	50	0.5	-55 to +125	ϕ 30	35	V _{(BR)R} ×0.9	80	50	1300	75	0.3		TO-18 Can	
NDL5102C	50	0.5	-55 to +125	ϕ 30	35	V _{(BR)R} ×0.9	80	50	1300	75	0.3	Chip on carrier	Surface mount	
NDL5102P	50	0.5	-30 to +70	ϕ 30	35	V _{(BR)R} ×0.9	80	50	1300	75	0.3	With SMF	Pigtail	
NDL5500	10	0.5	-55 to +100	ϕ 50	70	V _{(BR)R} ×0.9	20	40	1300 1550	85 80	—	f _c = 1.0 GHz MIN.	TO-18 Can	
NDL5500C	10	0.5	-55 to +100	ϕ 50	70	V _{(BR)R} ×0.9	20	40	1300 1550	85 80	—	Chip on carrier f _c = 1.0 GHz MIN.	Surface mount	
NDL5500P	10	0.5	-40 to +70	ϕ 50	70	V _{(BR)R} ×0.9	20	40	1300 1550	85 80	—	With GI-50/125 f _c = 1.0 GHz MIN.	Pigtail	
OD8406	1.0	—	-40 to +80	—	205	50	0.2	700	850	75	1.5		Receptacle	
OD8409	0.5	—	-40 to +80	—	30	V _{(BR)R} ×0.9	0.2	40	1300	75	0.5		Receptacle	
OD8412	1.0	—	-40 to +80	—	205	50	0.2	700	850	75	1.5	With GI-62.5/125	Pigtail	
OD8456	0.5	—	-40 to +80	—	30	V _{(BR)R} ×0.9	0.2	40	1300	75	0.5	With GI-62.5/125	Pigtail	

**MAX.